UTC 2SA684 PNP EPITAXIAL PLANAR TRANSISTOR

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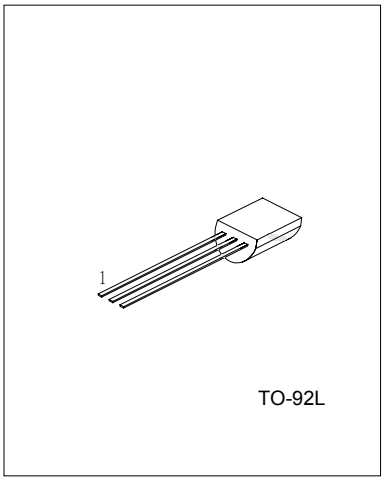
DESCRIPTION

The UTC 2SA684 is power amplifier and driver.

FEATURES

*Automatic insertion by radial taping possible.

*Complementary pair with 2SC1384



1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C ,unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Collector Current	Icp	1.5	A
Collector Current(DC)	Ic	1	A
Collector Dissipation(Ta=25°C)	Pc	1	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current	I_{CBO}	V_{CB}=20V,I_E=0			0.1	μA
Collector-Base Voltage	V_{CBO}	Ic=10μA,$I_{E=0}$	60			V
Collector-Emitter Voltage	V_{CEO}	Ic=2mA,I_B=0	50			V
Emitter-Base Voltage	V_{EBO}	I_E=10μA,Ic=0	5			V
DC Current Gain	h_{FE1}	V_{CE}=10V,Ic=500mA	85		340	
	h_{FE2}	V_{CE}=5V,I_B=1A	50			
Collector-Emitter Saturation Voltage	V_{CE}(sat)	Ic=0.5A,I_B=50mA		0.2	0.4	V
Base-Emitter Saturation Voltage	V_{BE}(sat)	Ic=0.5A,I_B=50mA		0.85	1.2	V
Current Gain Bandwidth Product	f_T	V_{CE}=10V,I_B=50mA,f=200MHz		200		MHz
Output Capacitance	Cob	V_{CB}=10V,I_E=0,f=1MHz		20	30	pF

CLASSIFICATION OF hFE

RANK	Q	R	S
RANGE	85-170	120-240	170-340